

# 2SA562 -0.5A, -35V PNP Plastic Encapsulated Transistor

#### RoHS Compliant Product

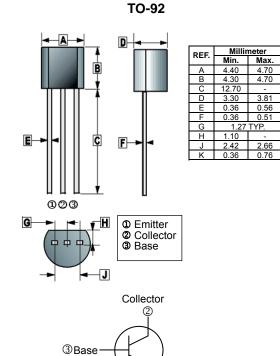
A suffix of "-C" specifies halogen & lead-free

### **FEATURES**

Excellent h<sub>FE</sub> Linearity

## **CLASSIFICATION OF h**<sub>FE</sub>

Product-Rank	2SA562-O	2SA562-Y
Range	70~140	120~240



Emitter

# $\textbf{ABSOLUTE MAXIMUM RATINGS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ specified)$

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	-35	V
Collector to Emitter Voltage	$V_{CEO}$	-30	V
Emitter to Base Voltage	$V_{EBO}$	-5	V
Collector Current - Continuous	Ic	-500	mA
Collector Power Dissipation	Pc	500	mW
Junction, Storage Temperature	T <sub>J</sub> , T <sub>STG</sub>	150, -55~150	°C

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub>=25°C unless otherwise specified)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Collector to Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-35	-	-	V	$I_C = -100 \mu A, I_E = 0A$
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	-30	-	-	V	$I_C$ = -1mA, $I_B$ = 0A
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-	-	V	$I_E = -100 \mu A, I_C = 0A$
Collector Cut-Off Current	I <sub>CBO</sub>	-	-	-0.1	μΑ	$V_{CB} = -35 \text{ V}, I_{E} = 0 \text{ A}$
Emitter Cut-Off Current	I <sub>EBO</sub>	-	-	-0.1	μΑ	$V_{EB}$ = -5 V, $I_C$ = 0 mA
DC Current Gain	h <sub>FE</sub>	70	-	240		V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>	-	-	-0.25	V	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA
Base to Emitter Voltage	$V_{BE}$	-	-	-1	V	V <sub>CE</sub> = -1V , I <sub>C</sub> = -100mA
Transition Frequency	f⊤	-	200	-	MHz	$V_{CE} = -6V, I_{C} = -20mA$
Collector output capacitance	C <sub>ob</sub>	-	13	-	pF	$V_{CB}$ = -6V, $I_E$ = 0A, f= 1MHz

http://www.SeCoSGmbH.com/

Any changes of specification will not be informed individually.

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### **CHARACTERISTIC CURVES**

